Preferred Devices

Sensitive Gate Silicon Controlled Rectifiers

Reverse Blocking Thyristors

Glassivated PNPN devices designed for high volume consumer applications such as temperature, light, and speed control; process and remote control, and warning systems where reliability of operation is important.

Features

- Pb-Free Packages are Available*
- Glassivated Surface for Reliability and Uniformity
- Power Rated at Economical Prices
- Practical Level Triggering and Holding Characteristics
- Flat, Rugged, Thermopad Construction for Low Thermal Resistance, High Heat Dissipation and Durability
- Sensitive Gate Triggering
- Device Marking: Device Type, e.g., C106B, Date Code



ON Semiconductor®

http://onsemi.com

SCRs 4 A RMS, 200 – 600 V





TO-225AA CASE 077 STYLE 2

MARKING DIAGRAM & PIN ASSIGNMENT

Gate 3 Anode 2 Cathode 1

 $xx = B, D, D1, D1G^*, M, MG^*, M1$

 $egin{array}{ll} Y &= Year \\ WW &= Work Week \\ G^* &= Pb-Free \\ \end{array}$

ORDERING INFORMATION

Device	Package	Shipping [†]
C106B	TO225AA	500/Box
C106D	TO225AA	500/Box
C106D1**	TO225AA	500/Box
C106D1G	TO225AA (Pb-Free)	500/Box
C106M	TO225AA	500/Box
C106MG	TO225AA (Pb-Free)	500/Box
C106M1**	TO225AA	500/Box

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Preferred devices are recommended choices for future use and best overall value.

^{**}D1 signifies European equivalent for D suffix and M1 signifies European equivalent for M suffix.

^{*}For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Characteristic		Symbol	Max	Unit	
Peak Repetitive Off–State Voltage (Note 1) (Sine Wave, 50–60 Hz, R_{GK} = 1 k Ω , T_{C} = -40° to 110°C)	e Wave, 50–60 Hz, $R_{GK} = 1 k\Omega$, V_{RRM}			V	
	C106B C106D, C106D1* C106M, C106M1*		200 400 600		
On-State RMS Current (180° Conduction Angles, T _C = 80°C)		I _{T(RMS)}	4.0	А	
Average On–State Current (180° Conduction Angles, T _C = 80°C)		I _{T(AV)}	2.55	А	
Peak Non-Repetitive Surge Current (1/2 Cycle, Sine Wave, 60 Hz, T _J = +110°C)		I _{TSM}	20	А	
Circuit Fusing Considerations (t = 8.3 ms)		l ² t	1.65	A ² s	
Forward Peak Gate Power (Pulse Width ≤ 1.0 µsec, T _C = 80°C)		P _{GM}	0.5	W	
Forward Average Gate Power (Pulse Width ≤ 1.0 µsec, T _C = 80°C)		P _{G(AV)}	0.1	W	
Forward Peak Gate Current (Pulse Width ≤ 1.0 µsec, T _C = 80°C)		I _{GM}	0.2	А	
Operating Junction Temperature Range		TJ	-40 to +110	°C	
Storage Temperature Range		T _{stg}	-40 to +150	°C	
Mounting Torque (Note 2)		_	6.0	in. lb.	

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise noted.)

Characteristic		Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	3.0	°C/W
Thermal Resistance, Junction to Ambient		75	°C/W
Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 10 Seconds		260	°C

^{*}D1 signifies European equivalent for D suffix and M1 signifies European equivalent for M suffix.

V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

^{2.} Torque rating applies with use of compression washer (B52200F006). Mounting torque in excess of 6 in. lb. does not appreciably lower case-to-sink thermal resistance. Anode lead and heatsink contact pad are common.

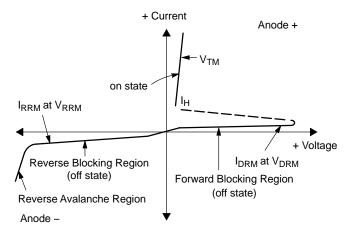
ELECTRICAL CHARACTERISTICS ($T_C = 25$ °C unless otherwise noted.)

Characteristic		Symbol	Min	Тур	Max	Unit	
OFF CHARACTERISTICS							
Peak Repetitive Forward or Reverse Blocking Current (V_{AK} = Rated V_{DRM} or V_{RRM} , R_{GK} = 1000 Ohms)	T _J = 25°C T _J = 110°C	I _{DRM} , I _{RRM}	_ _	_ _	10 100	μ Α μ Α	
ON CHARACTERISTICS							
Peak Forward On–State Voltage (Note 3) (I _{TM} = 4 A)		V _{TM}	-	_	2.2	Volts	
Gate Trigger Current (Continuous dc) (Note 4) (V _{AK} = 6 Vdc, R _L = 100 Ohms)	$T_J = 25$ °C $T_J = -40$ °C	I _{GT}	_ _	15 35	200 500	μΑ	
Peak Reverse Gate Voltage (I _{GR} = 10 μA)		V_{GRM}	_	_	6.0	Volts	
Gate Trigger Voltage (Continuous dc) (Note 4) (V _{AK} = 6 Vdc, R _L = 100 Ohms)	$T_{J} = 25^{\circ}C$ $T_{J} = -40^{\circ}C$	V _{GT}	0.4 0.5	0.60 0.75	0.8 1.0	Volts	
Gate Non–Trigger Voltage (Continuous dc) (Note 4) $(V_{AK} = 12 \text{ V}, R_L = 100 \text{ Ohms}, T_J = 110^{\circ}\text{C})$		$V_{\sf GD}$	0.2	_	-	Volts	
Latching Current (V _{AK} = 12 V, I _G = 20 mA)	T _J = 25°C T _J = -40°C	IL.	_ _	0.20 0.35	5.0 7.0	mA	
Holding Current (V _D = 12 Vdc) (Initiating Current = 20 mA, Gate Open)	$T_J = 25^{\circ}C$ $T_J = -40^{\circ}C$ $T_J = +110^{\circ}C$	lн	_ _ _	0.19 0.33 0.07	3.0 6.0 2.0	mA	
DYNAMIC CHARACTERISTICS							
Critical Rate-of-Rise of Off-State Voltage (V _{AK} = Rated V _{DRM} , Exponential Waveform, R _{GK} = 10 T _J = 110°C)	00 Ohms,	dv/dt	_	8.0	_	V/µs	

Pulse Test: Pulse Width ≤ 2.0 ms, Duty Cycle ≤ 2%.
 R_{GK} is not included in measurement.

Voltage Current Characteristic of SCR

Symbol	Parameter
V_{DRM}	Peak Repetitive Off State Forward Voltage
I _{DRM}	Peak Forward Blocking Current
V_{RRM}	Peak Repetitive Off State Reverse Voltage
I _{RRM}	Peak Reverse Blocking Current
V_{TM}	Peak On State Voltage
I _H	Holding Current



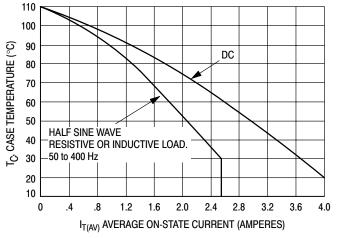


Figure 1. Average Current Derating

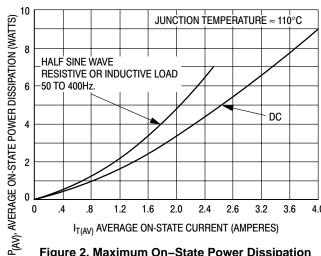


Figure 2. Maximum On-State Power Dissipation

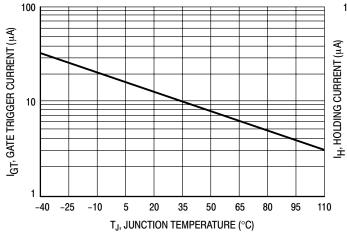


Figure 3. Typical Gate Trigger Current versus **Junction Temperature**

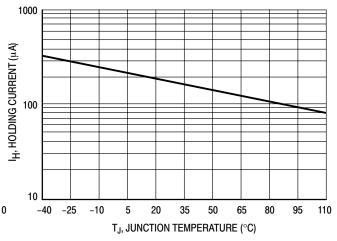


Figure 4. Typical Holding Current versus **Junction Temperature**

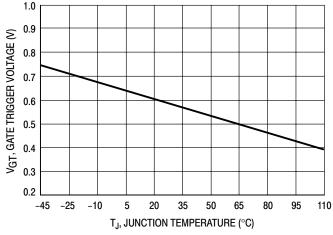


Figure 5. Typical Gate Trigger Voltage versus **Junction Temperature**

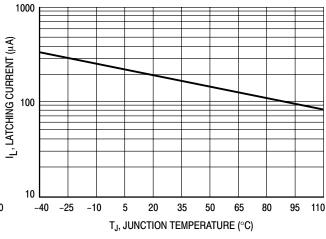
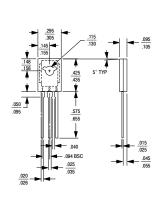


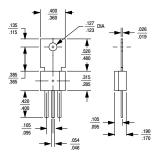
Figure 6. Typical Latching Current versus **Junction Temperature**

Package Interchangeability

The dimensional diagrams below compare the critical dimensions of the ON Semiconductor C-106 package with competitive devices. It has been demonstrated that the smaller dimensions of the ON Semiconductor package make it compatible in most lead-mount and chassis-mount applications. The user is advised to compare all critical dimensions for mounting compatibility.



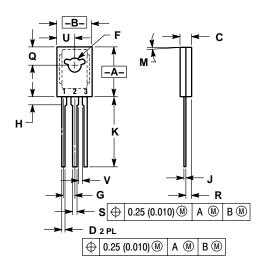
ON Semiconductor C-106 Package



Competitive C-106 Package

PACKAGE DIMENSIONS

TO-225AA (formerly TO-126) CASE 077-09 ISSUE Z



NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH.
 3. 077-01 THRU -08 OBSOLETE, NEW STANDARD

	INCHES		MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.425	0.435	10.80	11.04	
В	0.295	0.305	7.50	7.74	
С	0.095	0.105	2.42	2.66	
D	0.020	0.026	0.51	0.66	
F	0.115	0.130	2.93	3.30	
G	0.094 BSC		2.39 BSC		
Н	0.050	0.095	1.27	2.41	
J	0.015	0.025	0.39	0.63	
K	0.575	0.655	14.61	16.63	
M	5°	TYP	5° TYP		
Q	0.148	0.158	3.76	4.01	
R	0.045	0.065	1.15	1.65	
S	0.025	0.035	0.64	0.88	
U	0.145	0.155	3.69	3.93	
٧	0.040		1.02		

STYLE 2:

PIN 1. CATHODE

- ANODE
- 2. 3. GATE

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